# RF Transistor 12 V, 150 mA, f<sub>T</sub> = 7 GHz, NPN Single

This RF transistor is designed for low noise amplifier applications. CPH package is suitable for use under high temperature environment because it has superior heat radiation characteristics. This RF transistor is AEC-Q101 qualified and PPAP capable for automotive applications.

### **Features**

- High Gain (f<sub>T</sub> = 7 GHz typ)
- High Current (I<sub>C</sub> = 150 mA)
- Miniature and Thin 6 pin Package
- Large Collector Dissipation (800 mW)
- AEC-Q101 qualified and PPAP capable
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

- Low Noise Amplifier for FM Radio
- Low Noise Amplifier for TV

#### **SPECIFICATIONS**

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	VCBO	20	V
Collector to Emitter Voltage	VCEO	12	<b>V</b>
Emitter to Base Voltage	VEBO	2	٧
Collector Current	IC	150	mA
Collector Dissipation (Note 2)	PC	800	mW
Operating Junction and Storage Temperature	Tj, Tstg	−55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Surface mounted on ceramic substrate (250 mm<sup>2</sup> × 0.8 mm).

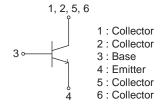


ON Semiconductor®

www.onsemi.com

12 V, 150 mA fT = 7 GHz typ. RF Transistor

# ELECTRICAL CONNECTION NPN



#### **MARKING**





#### ORDERING INFORMATION

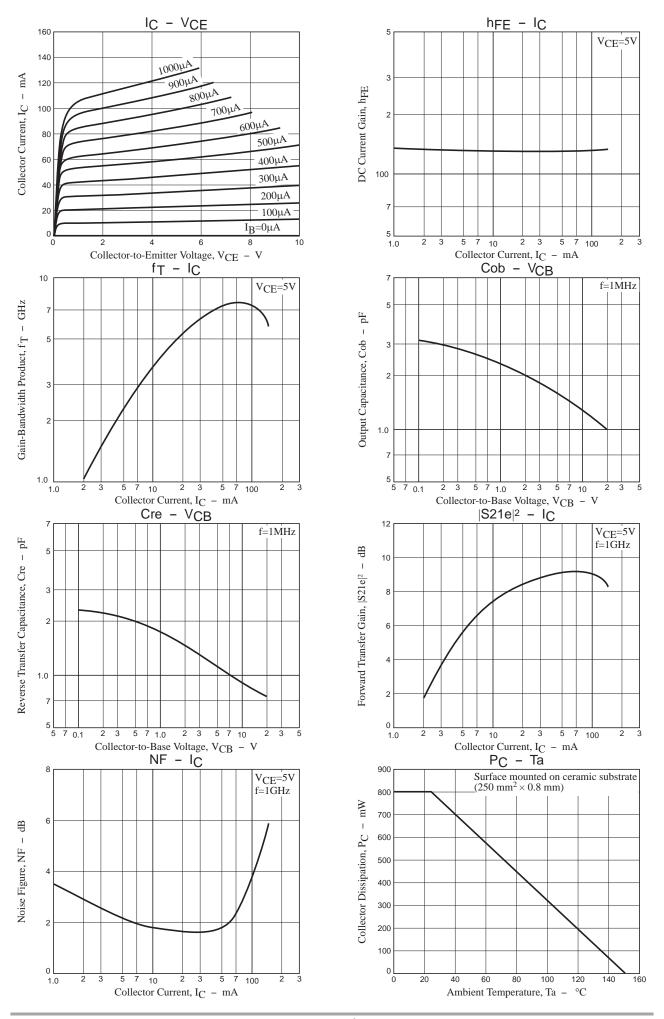
See detailed ordering and shipping information on page 6 of this data sheet.

### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 3)

Parameter	Symbol	Conditions		Unit		
Farameter	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0 A			1.0	μΑ
Emitter Cutoff Current	IEBO	VEB = 1 V, IC = 0 A			10	μΑ
DC Current Gain	hFE	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	100		180	
Gain-Bandwidth Product	fŢ	VCE = 5 V, IC = 50 mA		7		GHz
Output Capacitance	Cob	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		1.3	2.0	pF
Reverse Transfer Capacitance	Cre	VCB = 10 V, f = 1 MHz		0.9		pF
Forward Transfer Gain	S21e   <sup>2</sup>	VCE = 5 V, IC = 50 mA, f = 1 GHz		9.0		dB
Noise Figure	NF	VCE = 5 V, IC = 5 0mA, f = 1 GHz		1.8	3.0	dB

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 4: Pay attention to handling since it is liable to be affected by static electricity due to the high-frequency process adopted.



# S Parameters (Common emitter)

 $V_{CE}$  = 5 V, I<sub>C</sub> = 20 mA, Z<sub>O</sub> = 50  $\Omega$ 

Freq(MHz)	S <sub>11</sub>	∠S <sub>11</sub>	S <sub>21</sub>	∠S <sub>21</sub>	S <sub>12</sub>	∠S <sub>12</sub>	S <sub>22</sub>	∠S <sub>22</sub>
100	0.550	254.1	21.532	119.9	0.036	54.6	0.527	-62.8
200	0.492	218.1	12.273	103.0	0.050	56.5	0.332	-80.3
300	0.477	201.9	8.448	95.3	0.063	61.7	0.267	-88.3
400	0.470	192.4	6.427	90.4	0.078	65.3	0.242	268.1
500	0.518	181.0	5.015	86.8	0.089	68.2	0.217	245.3
600	0.513	175.8	4.221	83.9	0.104	70.2	0.216	245.8
700	0.510	171.5	3.658	81.3	0.120	71.7	0.214	247.2
800	0.508	167.6	3.234	78.9	0.135	72.7	0.220	249.3
900	0.503	163.7	2.900	76.7	0.150	73.2	0.225	251.3
1000	0.497	160.1	2.636	74.4	0.166	73.7	0.231	254.6
1100	0.493	156.8	2.419	72.5	0.181	73.9	0.239	256.3
1200	0.489	153.4	2.243	70.5	0.196	74.1	0.247	258.8

# $V_{\mbox{\footnotesize{CE}}}$ = 5 V, $I_{\mbox{\footnotesize{C}}}$ = 50 mA, $Z_{\mbox{\footnotesize{O}}}$ = 50 $\Omega$

Freq(MHz)	S <sub>11</sub>	∠S <sub>11</sub>	S <sub>21</sub>	∠S <sub>21</sub>	S <sub>12</sub>	∠S <sub>12</sub>	S <sub>22</sub>	∠S <sub>22</sub>
100	0.465	231.1	25.203	111.9	0.029	59.2	0.413	-79.9
200	0.449	203.4	13.519	98.7	0.045	65.7	0.269	259.6
300	0.445	191.6	9.177	92.7	0.061	70.4	0.230	250.7
400	0.443	184.2	6.947	88.8	0.078	72.8	0.218	247.3
500	0.502	175.0	5.407	86.1	0.092	74.7	0.231	224.3
600	0.497	170.3	4.550	83.7	0.110	75.6	0.229	225.5
700	0.494	166.4	3.944	81.5	0.127	76.2	0.225	227.1
800	0.490	162.8	3.483	79.4	0.144	76.4	0.228	229.9
900	0.485	159.1	3.127	77.4	0.161	76.2	0.230	232.4
1000	0.478	155.5	2.845	75.5	0.178	76.1	0.230	236.1
1100	0.473	152.3	2.608	73.6	0.195	75.9	0.236	238.6
1200	0.468	149.0	2.423	71.9	0.211	75.5	0.239	242.0

# $V_{CE}$ = 5 V, $I_{C}$ = 100 mA, $Z_{O}$ = 50 $\Omega$

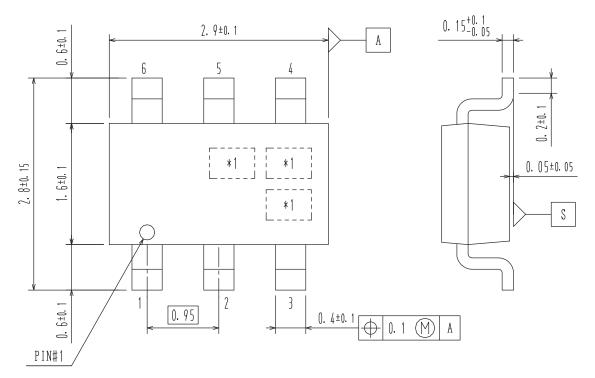
Freq(MHz)	S <sub>11</sub>	∠s <sub>11</sub>	S <sub>21</sub>	∠S <sub>21</sub>	S <sub>12</sub>	∠S <sub>12</sub>	S <sub>22</sub>	∠S <sub>22</sub>
100	0.451	219.5	25.808	108.5	0.026	62.4	0.359	-86.7
200	0.448	196.7	13.593	96.8	0.043	69.8	0.240	253.1
300	0.448	187.0	9.193	91.4	0.060	73.8	0.212	244.9
400	0.446	180.7	6.953	87.8	0.078	75.5	0.205	242.3
500	0.508	172.6	5.408	85.5	0.093	76.9	0.228	219.9
600	0.503	168.3	4.550	83.1	0.110	77.5	0.226	221.5
700	0.500	164.6	3.944	81.0	0.128	77.8	0.223	223.4
800	0.497	161.2	3.480	79.0	0.145	77.8	0.226	226.5
900	0.490	157.6	3.132	77.0	0.163	77.4	0.228	229.1
1000	0.484	154.2	2.842	75.0	0.180	77.1	0.227	233.1
1100	0.479	151.0	2.614	73.3	0.197	76.7	0.232	235.8
1200	0.473	147.8	2.423	71.6	0.214	76.3	0.236	239.3

## PACKAGE DIMENSIONS

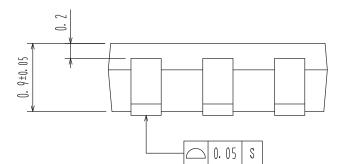
unit: mm

### CPH6

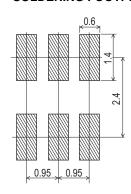
CASE 318BD ISSUE O



### \*1:Lot indication



### **RECOMMENDED SOLDERING FOOTPRINT**



- 1 : Collector 2 : Collector
- 3 : Base
- 4 : Emitter
- 5 : Collector
- 6: Collector

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)
NSVF6003SB6T1G	GC	CPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: NSVF6003SB6T1G